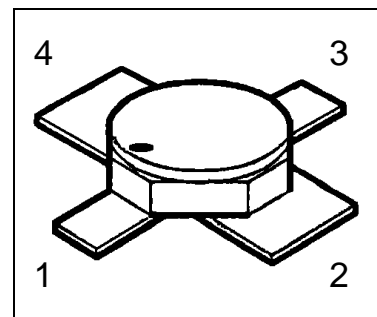


HiRel NPN Silicon RF Transistor

BFY740B-02(ES)

Features

- High gain ultra low noise RF transistor
- Outstanding noise figure
 - $F = 0.65 \text{ dB}$ at 1.8 GHz
 - $F = 1.05 \text{ dB}$ at 6 GHz
 - $F = 1.50 \text{ dB}$ at 10 GHz
 - $F = 1.60 \text{ dB}$ at 12 GHz
- Hermetically sealed microwave package



Product validation

-  **ESA Space Qualified**
 ESCC Detail Spec. No.: 5611/011
 Type Variant No. 02

Description

ESD: Electrostatic discharge sensitive device,
observe handling precautions!

Table 1 **Product information**

| Type | Comment | Pin Configuration | | | | Package |
|----------------------------|---------------------------------|-------------------|---|---|---|---------|
| | | 1 | 2 | 3 | 4 | |
| BFY740B-02(ES) | For flight use | C | E | B | E | Micro-X |
| BFY740B-02(P) ¹ | Not for flight use ¹ | | | | | |

¹ (P) parts have the same fit, form and function as (ES) parts,
no screening acc. to Chart F3 in ESCC Generic Specification No. 5010

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Maximum ratings

1 Maximum ratings

Table 2 Maximum ratings

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|--------------------------------------|-----------|--------|------|----------|------|---|
| | | Min. | Typ. | Max. | | |
| Collector-emitter voltage | V_{CEO} | - | - | 4 3.5 | V | $T_A > 0\text{ °C}$ $T_A \leq 0\text{ °C}$ |
| Collector-base voltage | V_{CBO} | - | - | 13 | V | |
| Emitter-base voltage | V_{EBO} | - | - | 1.2 | V | |
| Collector current | I_C | - | - | 30 | mA | |
| Base current ¹ | I_B | - | - | 3 | mA | |
| Total power dissipation ² | P_{tot} | - | - | 120 | mW | $T_S \leq 125\text{ °C}$ |
| Junction temperature | T_j | - | - | 175 | °C | |
| Operating temperature | T_{op} | -65 | - | 175 | °C | |
| Storage temperature | T_{stg} | -65 | - | 175 | °C | |

¹ Maximum ratings must not be exceeded under any combination of DC ratings and RF voltage/current swings except as specified in §3

² For $T_S > 125\text{ °C}$ derating is required. T_S is measured on the collector lead at the soldering point to the PCB

Thermal characteristics

2 Thermal characteristics

Table 3 Thermal characteristics

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|--|-------------|--------|------|------|------|--|
| | | Min. | Typ. | Max. | | |
| Thermal resistance, junction –soldering point | $R_{th,JS}$ | - | - | 400 | K/W | T_s is measured on the collector lead at the soldering point to the PCB |
| Soldering Temperature | T_{sol} | - | - | 250 | °C | Duration 5 seconds maximum at a distance of not less than 0.5mm from the device body and the same lead shall not be resoldered until 3 minutes have elapsed. |

3 Electrical characteristics

at $T_A=25^\circ\text{C}$, unless otherwise specified

Table 4 Static characteristics

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|---|-----------|--------|------|------|---------------|--|
| | | Min. | Typ. | Max. | | |
| Collector-base cutoff current | I_{CBO} | - | - | 10 | μA | $V_{CB} = 5\text{V}, I_E = 0\text{A}$ |
| Collector-emitter cutoff current ¹ | I_{CEX} | - | - | 200 | μA | $V_{CE} = 4\text{V}, I_B = 0.1\mu\text{A}$ |
| Emitter base cutoff current | I_{EBO} | - | - | 5 | μA | $V_{EB} = 1.2\text{V}, I_C = 0\text{A}$ |
| DC current gain | h_{FE} | 170 | 280 | 400 | - | $I_C = 20\text{mA}, V_{CE} = 3\text{V}$ |

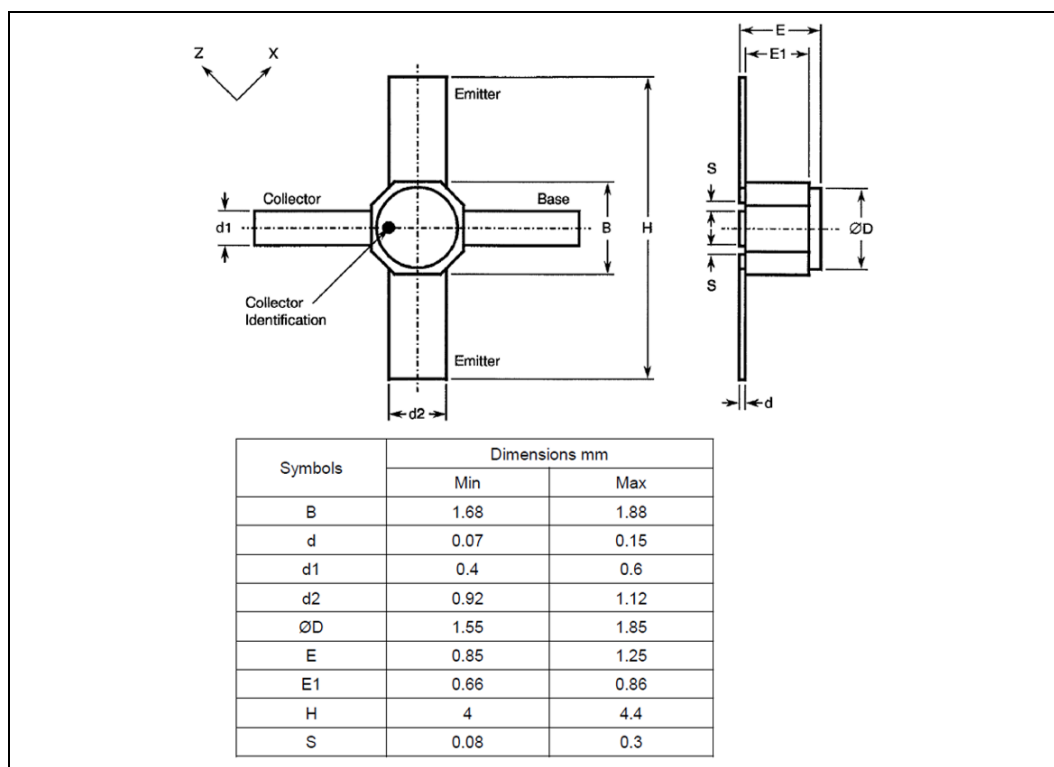
Table 5 Dynamic characteristics

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|--|---------------|--------|----------------------------|------|------|--|
| | | Min. | Typ. | Max. | | |
| Collector-base capacitance | C_{CB} | - | 0.07 | - | pF | $V_{CB} = 2\text{V}, V_{BE} = v_{be} = 0, f = 1\text{MHz}$ |
| Collector-emitter capacitance | C_{CE} | - | 0.45 | - | pF | $V_{CE} = 2\text{V}, V_{BE} = v_{be} = 0, f = 1\text{MHz}$ |
| Emitter-base capacitance | C_{EB} | - | 0.6 | - | pF | $V_{EB} = 0.5\text{V}, V_{CB} = v_{cb} = 0, f = 1\text{MHz}$ |
| Noise Figure ($Z_S = Z_{Sopt}$) | F | - | 0.65 1.05 1.5 1.6 | - | dB | $I_C = 8\text{mA}, V_{CE} = 3\text{V}, f = 1.8\text{GHz}$ $I_C = 8\text{mA}, V_{CE} = 3\text{V}, f = 6.0\text{GHz}$ $I_C = 8\text{mA}, V_{CE} = 3\text{V}, f = 10\text{GHz}$ $I_C = 8\text{mA}, V_{CE} = 3\text{V}, f = 12\text{GHz}$ |
| Insertion power gain ($Z_S = Z_L = 50\Omega$) | $ S_{21e} ^2$ | - | 24 14 9 7 | - | dB | $I_C = 20\text{mA}, V_{CE} = 3\text{V}, f = 1.8\text{GHz}$ $I_C = 20\text{mA}, V_{CE} = 3\text{V}, f = 6.0\text{GHz}$ $I_C = 20\text{mA}, V_{CE} = 3\text{V}, f = 10\text{GHz}$ $I_C = 20\text{mA}, V_{CE} = 3\text{V}, f = 14\text{GHz}$ |
| Power Gain ² | G_{ms} | - | 26.5 | - | dB | $I_C = 20\text{mA}, V_{CE} = 3\text{V}, f = 1.8\text{GHz},$ $Z_S = Z_{Sopt}, Z_L = Z_{Lopt}$ |
| Power Gain ² | G_{ma} | - | 19 15 | - | dB | $I_C = 20\text{mA}, V_{CE} = 3\text{V}, f = 6.0\text{GHz},$ $Z_S = Z_{Sopt}, Z_L = Z_{Lopt}$ $I_C = 20\text{mA}, V_{CE} = 3\text{V}, f = 10\text{GHz},$ $Z_S = Z_{Sopt}, Z_L = Z_{Lopt}$ |
| Output power | P_{out} | - | 14.8 | - | dBm | $I_C = 20\text{mA}, V_{CE} = 3\text{V}, f = 1.8\text{GHz},$ $P_{in} = 0\text{ dBm}$ |

¹ This test assures $V_{(BR)CE0} > 4\text{V}$

² $G_{ma} = \left| \frac{S_{21}}{S_{12}} \right| (k - \sqrt{k^2 - 1})$, $G_{ms} = \left| \frac{S_{21}}{S_{12}} \right|$

4 Package outlines



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